

L Number	Hits	Search Text	DB	Time stamp
-	19	block adj mold\$3 and semiconductor and clean\$3	USPAT	2003/06/04 12:09
-	0	mold\$3 and semiconductor near4 clean\$3 same rie same roughen\$	USPAT	2003/01/06 12:57
-	1	mold\$3 and semiconductor near4 clean\$3 same plasma same roughen\$	USPAT	2003/01/06 11:05
-	0	mold\$3 and semiconductor same substrate near4 clean\$3 same plasma same roughen\$	USPAT	2003/01/06 11:29
-	27	mold\$3 and semiconductor same substrate near4 clean\$3 same plasma	USPAT	2003/01/06 12:49
-	0	"6200121" and fr4	USPAT	2004/02/19 11:50
-	86	mold\$4 same fr4	USPAT	2003/01/06 12:51
-	0	mold\$3 and fr4 same semiconductor near4 clean\$3	USPAT	2003/01/06 13:01
-	69	mold\$3 and fr4 same semiconductor	USPAT	2003/01/06 13:01
-	1	"6200121" and clean\$	USPAT	2003/01/06 14:15
-	1	"6200121" and clean\$4	USPAT	2004/02/19 11:49
-	30	multiple same stack\$3 same chips same encapsulat\$4	USPAT	2003/01/06 15:25
-	0	6414384.URPN.	USPAT	2003/01/06 15:24
-	95	stack\$3 near chip same encapsulat\$4	USPAT	2003/01/06 15:58
-	22	"5973403"	USPAT	2003/01/06 16:14
-	11	("4900501" "4983110" "5490324" "5656549" "5961912" "6013947" "6014318" "6031281" "6114189" "6164946" "6173490").PN.	USPAT	2003/01/06 16:11
-	2	6338813.URPN.	USPAT	2003/01/06 16:12
-	7311	(encapsulat\$4 or mold\$4) and semiconductor and clean\$3	USPAT	2003/06/04 14:13
-	75	(encapsulat\$4 or mold\$4) and semiconductor and clean\$3 and silica adj filler\$1	USPAT	2003/06/04 15:49
-	20	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 volume near3 (percent or "%")	USPAT	2003/06/04 16:18
-	4	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 volume near3 (percent or "%")	US-PGPUB	2003/06/04 16:18
-	183	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 filler	US-PGPUB	2003/06/04 16:06
-	91	(encapsulat\$4 or mold\$4) and semiconductor and silica near filler	US-PGPUB	2003/06/04 16:07
-	1	(encapsulat\$4 or mold\$4) and semiconductor and silica near filler and gotou	US-PGPUB	2003/06/04 16:07
-	4	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 vol near3 (percent or "%")	US-PGPUB	2003/06/04 16:19
-	20	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 vol near3 (percent or "%")	USPAT	2003/06/04 16:19
-	20	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 vol near3 (percent or "%" or pct)	USPAT	2003/06/04 16:19
-	4	(encapsulat\$4 or mold\$4) and semiconductor and silica near3 vol near3 (percent or "%" or pct)	US-PGPUB	2003/06/04 16:19
-	3	(encapsulat\$4 or mold\$4) and semiconductor and silica near filler near6 vol near3 (percent or "%" or pct)	USPAT	2003/06/04 16:28
-	4	silica near filler near6 (vol or volume) near3 (percent or "%" or pct) same (weight or wt) near3 (percent or "%" or pct)	USPAT	2003/06/04 16:27
-	7	"6200121"	USPAT	2004/02/19 14:18
-	1	"6200121" and air adj vent\$	USPAT	2004/02/19 13:25